

Three Phase Half Controlled Bridges

PSDH 70

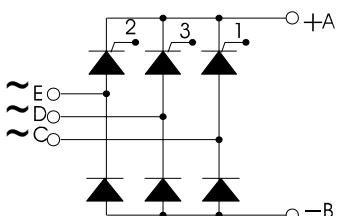
I_{dAV}
 V_{RRM}

= 70 A
= 400-1600 V

Preliminary Data Sheet

V_{RSM}	V_{RRM}	Type
V_{DSM}	V_{DRM}	
500	400	PSDH 70/04
900	800	PSDH 70/08
1300	1200	PSDH 70/12
1500	1400	PSDH 70/14
*1700	*1600	PSDH 70/16

* Delivery on request



Symbol	Test Conditions		Maximum Ratings		
I_{dAV}	$T_C = 85^\circ C$	per module	70	A	
I_{TSM}, I_{FSM}	$T_{VJ} = 45^\circ C$	$t = 10 \text{ ms}$ (50 Hz), sine	550	A	
	$V_R = 0$	$t = 8.3 \text{ ms}$ (60 Hz), sine	600	A	
	$T_{VJ} = T_{VJM}$	$t = 10 \text{ ms}$ (50 Hz), sine	500	A	
	$V_R = 0$	$t = 8.3 \text{ ms}$ (60 Hz), sine	550	A	
$\int i^2 dt$	$T_{VJ} = 45^\circ C$	$t = 10 \text{ ms}$ (50 Hz), sine	1520	$A^2 \text{ s}$	
	$V_R = 0$	$t = 8.3 \text{ ms}$ (60 Hz), sine	1520	$A^2 \text{ s}$	
	$T_{VJ} = T_{VJM}$	$t = 10 \text{ ms}$ (50 Hz), sine	1250	$A^2 \text{ s}$	
	$V_R = 0$	$t = 8.3 \text{ ms}$ (60 Hz), sine	1250	$A^2 \text{ s}$	
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$	repetitive, $I_T = 50 \text{ A}$	150	$A/\mu\text{s}$	
	$f = 50 \text{ Hz}$, $t_P = 200 \mu\text{s}$				
	$V_D = 2/3 V_{DRM}$				
	$I_G = 0.3 \text{ A}$	non repetitive, $I_T = \frac{1}{2} \cdot I_{dAV}$	500	$A/\mu\text{s}$	
	$dI_G/dt = 0.3 \text{ A}/\mu\text{s}$				
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$	$V_{DR} = 2/3 V_{DRM}$	1000	$V/\mu\text{s}$	
	$R_{GK} = \infty$, method 1 (linear voltage rise)				
P_{GM}	$T_{VJ} = T_{VJM}$	$t_P = 30 \mu\text{s}$	\leq	10	W
	$I_T = I_{TAVM}$	$t_P = 500 \mu\text{s}$	\leq	5	W
P_{GAVM}				0.5	W
V_{RGM}				10	V
T_{VJ}			-40 ... + 125		$^\circ C$
T_{VJM}			125		$^\circ C$
T_{stg}			-40 ... + 125		$^\circ C$
V_{ISOL}	50/60 HZ, RMS	$t = 1 \text{ min}$	2500	V ~	
	$I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ s}$	3000	V ~	
M_d	Mounting torque	(M5)	2 - 2.5	Nm	
Weight	typ.		100	g	

Features

- Package with fast-on terminals
- Isolation voltage 3000 V~
- Planar glasspassivated chips
- Low forward voltage drop
- UL registered E 148688

Applications

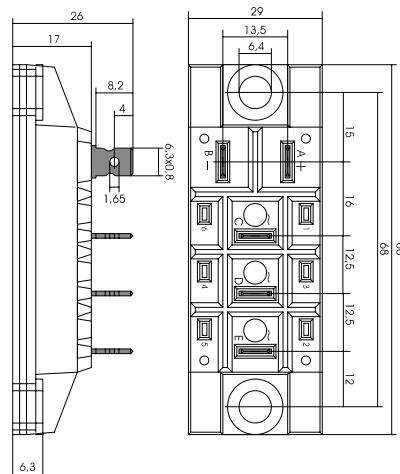
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Motor control
- Power converter

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density

Package, style and outline

Dimensions in mm (1mm = 0.0394")



Symbol	Test Conditions		Characteristic Value		
I_D, I_R	$T_{VJ} = T_{VJM}$, $V_R = V_{RRM}$, $V_D = V_{DRM}$		\leq	5	mA
V_T	$I_T = 80A$, $T_{VJ} = 25^\circ C$		\leq	1.64	V
V_{TO}	For power-loss calculations only ($T_{VJ} = T_{VJM}$)			0.85	V
r_T				11	$m\Omega$
V_{GT}	$V_D = 6V$	$T_{VJ} = 25^\circ C$	\leq	1.5	V
		$T_{VJ} = -40^\circ C$	\leq	1.6	V
I_{GT}	$V_D = 6V$	$T_{VJ} = 25^\circ C$	\leq	100	mA
		$T_{VJ} = -40^\circ C$	\leq	200	mA
V_{GD}	$T_{VJ} = T_{VJM}$	$V_D = 2/3 V_{DRM}$	\leq	0.2	V
I_{GD}	$T_{VJ} = T_{VJM}$	$V_D = 2/3 V_{DRM}$	\leq	5	mA
I_L	$T_{VJ} = 25^\circ C$, $t_P = 10\mu s$ $I_G = 0.45A$, $dI_G/dt = 0.45A/\mu s$		\leq	450	mA
I_H	$T_{VJ} = 25^\circ C$, $V_D = 6V$, $R_{GK} = \infty$		\leq	200	mA
t_{gd}	$T_{VJ} = 25^\circ C$, $V_D = 1/2 V_{DRM}$ $I_G = 0.45A$, $dI_G/dt = 0.45A/\mu s$		\leq	2	μs
t_q	$T_{VJ} = T_{VJM}$, $I_T = 20A$, $t_P = 200\mu s$, $V_R = 100V$ $-di/dt = 10A/\mu s$, $dv/dt = 15V/\mu s$, $V_D = 2/3 V_{DRM}$			250	μs
R_{thJC}	per thyristor; sine 180°el			0.9	K/W
	per module			0.15	K/W
R_{thJK}	per thyristor; sine 180° el			1.1	K/W
	per module			0.183	K/W
d_s	Creeping distance on surface			16.1	mm
d_A	Creeping distance in air			7.5	mm
a	Max. allowable acceleration			50	m/s^2

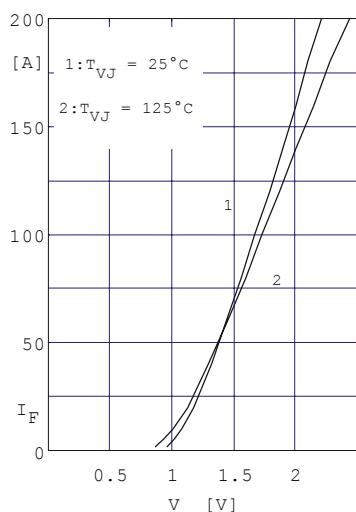


Fig. 1 Forward current vs. voltage drop per diode or thyristor

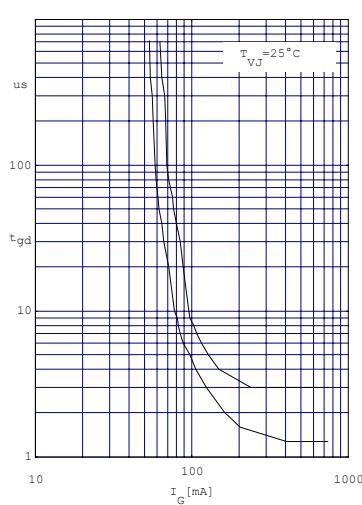


Fig. 2 Gate trigger delay time

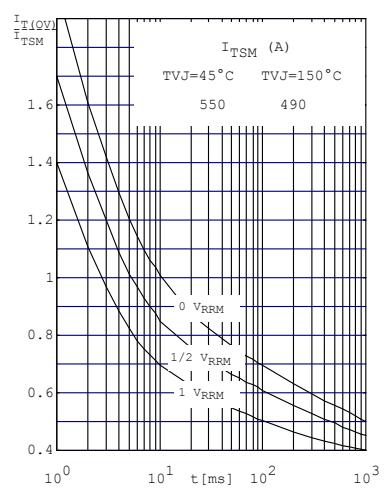


Fig. 3 Surge overload current per diode (or thyristor) I_{FSM} , I_{TSM} : Crest value t: duration

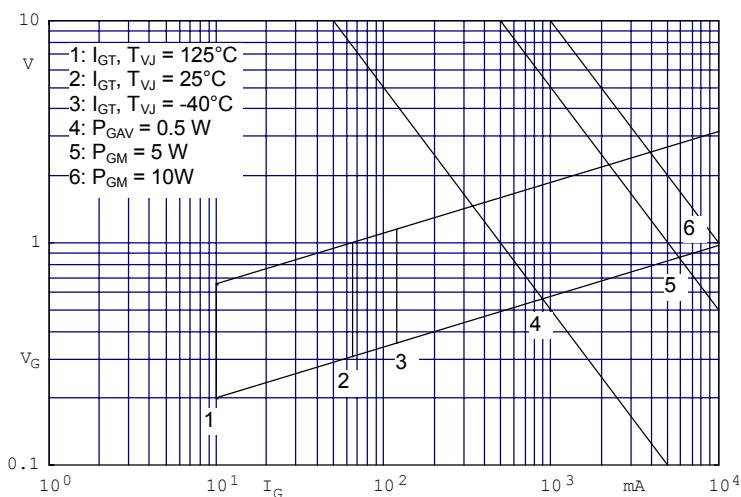


Fig.4 Gate trigger characteristic

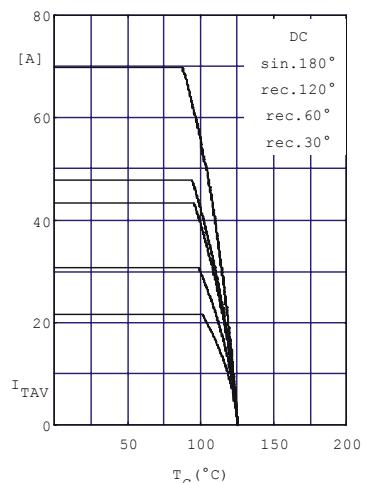


Fig.5 Maximum forward current at case temperature

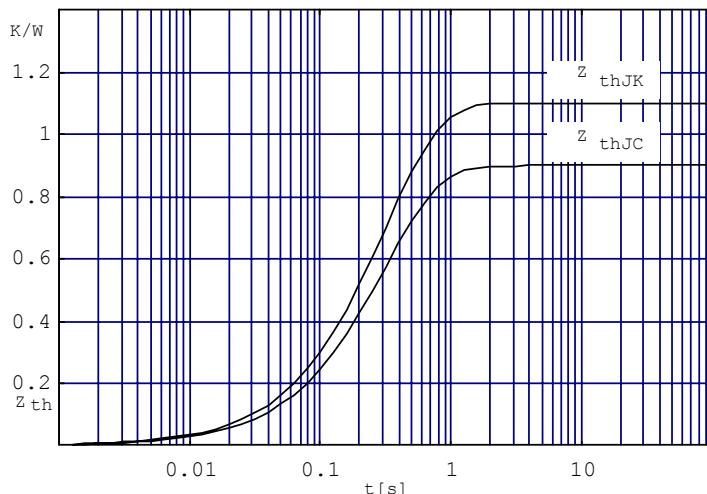


Fig.6 Transient thermal impedance per thyristor or diode

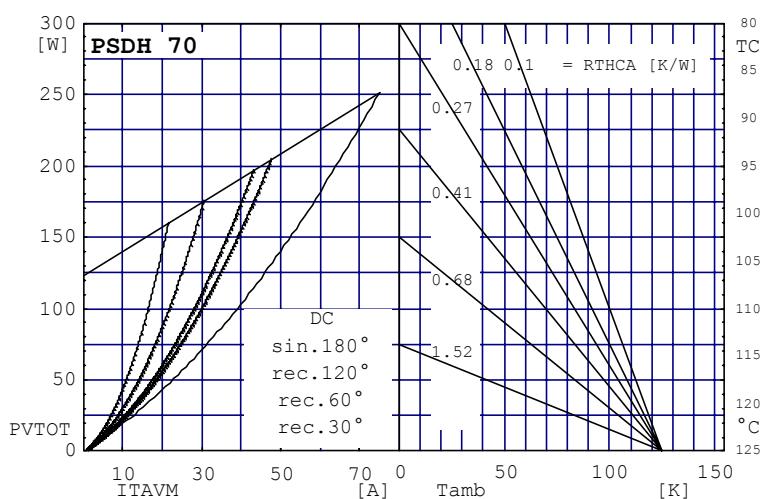


Fig. 7 Power dissipation vs. direct output current and ambient temperature